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Si-Ge 5 30 %, Si-Ge

Dense polycrystalline condensates of Si-Ge alloys were grown by reduced pressure CVD intended for usage as materials for thermoelectric energy converters. The kinetics of a Si-Ge deposition is researched. The presence of the small amounts of germanium intensifies the process of a silicon deposition. The determination of germanium concentration in the samples was made via the nuclear physics technique. The examination, made in the microanalyzer, attested to a high homogeneity of the Si-Ge condensates.

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Si-Ge $Si_{0,7}Ge_{0,3}$, [1].

Si-Ge [2].

, n- -

Si-Ge

CVD, Si-Ge,

[3]. , -

[4]. CVD , -

30%.

Ø 150 , 600 , -

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8 50 , -

80 10 1 , -

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900 -

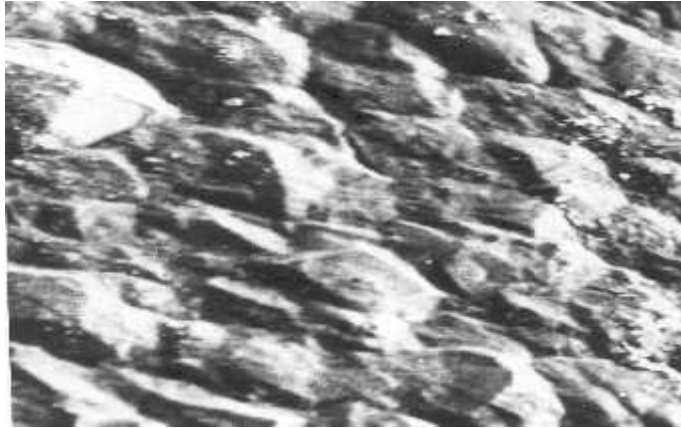
1200⁰

-

Si-Ge
 1200⁰
 Si-Ge : a)
 900⁰
 Si-Ge
 5 · 10⁻¹
 Si - Ge
 SiCl₄ - GeCl₄ - H₂ - HCl

0,1 – 50

()



Si-Ge

Si-Ge

50 – 760

5 %.

: **1.** Charles Wood. Refractory semiconductors for high temperature thermoelectric energy conversion. // Mat. Res. Soc. Symp. Proc. Vol.97. 1987 Materials Research Society. **2.** VI .. - , 1999, . 113. **3.** M. Kato, e. a. // Journal of Crystal Growth 115 (1991) 117 – 121 North-Holland. **4.** Choy K. L. Progress in Materials Science 2003, Vol 48, Iss 2.

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662.74

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In article results of research of reaction acylation amine by diphenolic anhydride are presented. Influence of solvent, duration of heating, basicity amine on an output and structure is considered. Received diphenolic acids malamic are of interest for their test for demonstration of various kinds of biological activity.

[1]

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